

P-Channel MOSFET Transistor

2SJ79K / J79K

200V / 0.5A

DATASHEET

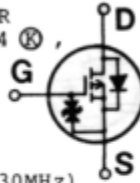
OEM – Hitachi

Source: Hitachi Databook Power Mosfet Data 4/83

2SJ77K, 2SJ79K

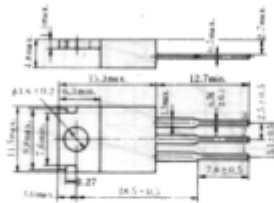
SILICON P-CHANNEL MOS FET

HIGH SPEED POWER SWITCHING,
HIGH FREQUENCY POWER AMPLIFIER
Complementary Pair with 2SK214 (K),
K216 (K)



Features;

- High Speed Switching.
- High Cutoff Frequency. ($f_c=30\text{MHz}$)
- High Breakdown Voltage.
- Suitable for Switching Regulator, DC-DC Converter, RF Amplifiers, and Ultrasonic Power Oscillators.



(Dimensions in mm)
(JEDEC TO-220AB)

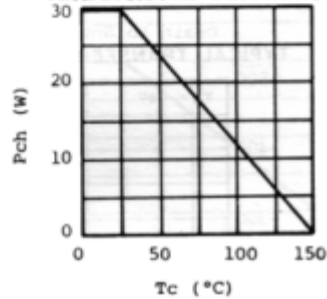
1. Gate
2. Source (Flange)
3. Drain

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Rating		Unit
		J77 (K)	J79 (K)	
Drain-Source Voltage	V _{DSX}	-160	-200	V
Gate-Source Voltage	V _{GS}	±15		V
Drain Current	I _D	-500		mA
Body-Drain Diode Reverse Drain Current	I _{DR}	-500		mA
Channel Dissipation	P _{ch}	1.75		W
	P _{ch} *	30		W
Channel Temperature	T _{ch}	150		°C
Storage Temperature	T _{stg}	-45 ~ +150		°C

*Value at Tc=25°C

POWER VS. TEMPERATURE DERATING



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	J77 (K)	I _D =-1mA, V _{GS} =2V	-160	-	-	V
	J79 (K)		-200	-	-	V
Gate-Source Breakdown Voltage	V _{(BR) GSS}	I _G =±10µA, V _{DS} =0	±15	-	-	V
Gate-Source Voltage	V _{GS (on)}	I _D =-10mA, V _{DS} =-10V*	-0.2	-	-1.5	V
Drain-Source Saturation Voltage	V _{DS (sat)}	I _D =-10mA, V _{GD} =0 *	-	-	-2.0	V
Forward Transfer Capacitance	Y _{fs}	I _D =-10mA, V _{DS} =-20V*	-	35	-	mS
Input Capacitance	C _{iss}	V _{DS} =-10V, I _D =-10mA,	-	120	-	pF
Reverse Transfer Capacitance	C _{rss}	f=1MHz	-	4.8	-	pF

*Pulse Test

2SJ77®.2SJ79®

